

EECS 16B

Designing Information Devices and Systems II

Lecture 8

Prof. Sayeef Salahuddin

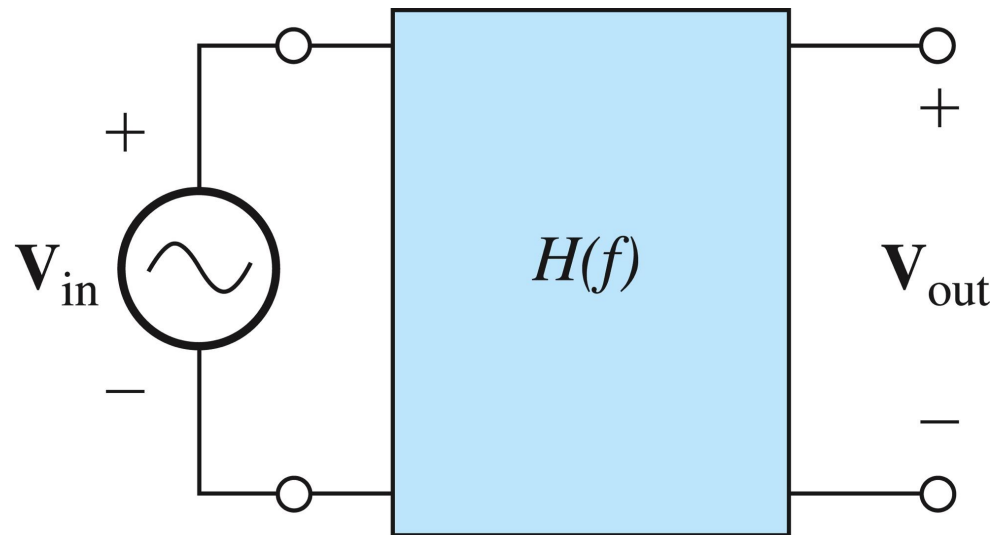
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Transient Response

- Outline
 - High Pass Filters
 - Series and Parallel Resonance
 - Amplifiers and Devices

- Reading- Hambley text sections 6.4, 6.5, 6.6, 6.7, slides

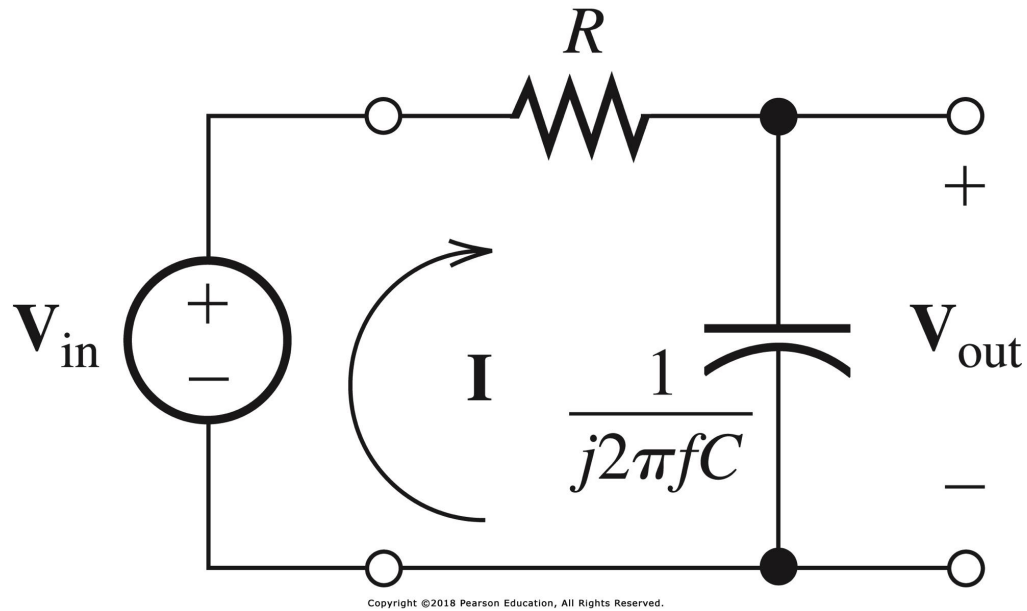
Recap: Concept of Transfer Function



$$H(f) = \frac{V_{out}}{V_{in}}$$

$H(f)$ is a complex number

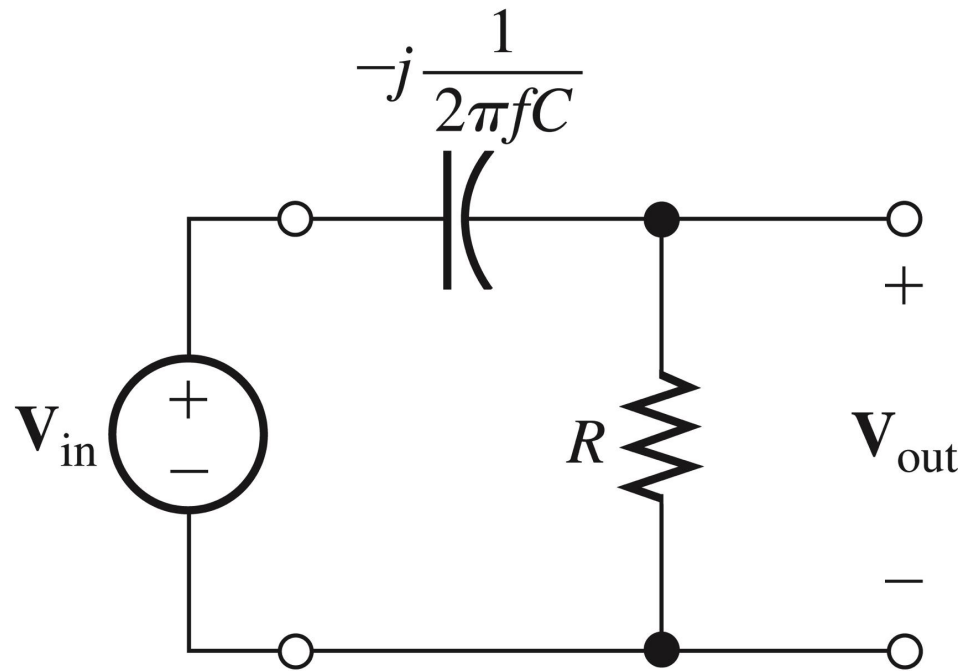
Recap: First order low pass filter



$$H(f) = \frac{1}{\sqrt{\left(1 + \frac{f^2}{f_B^2}\right)}} \angle -\tan^{-1}\left(\frac{f}{f_B}\right)$$

$$f_B = \frac{1}{2\pi RC}$$

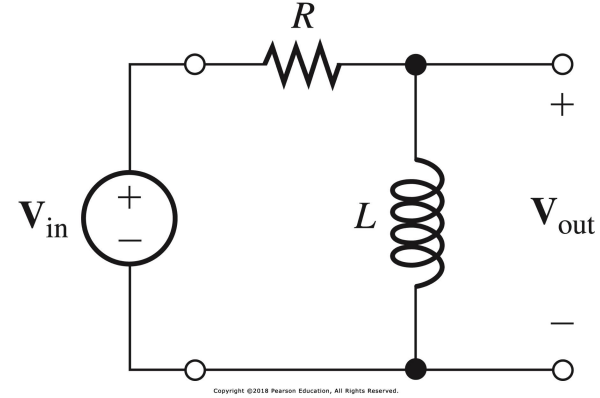
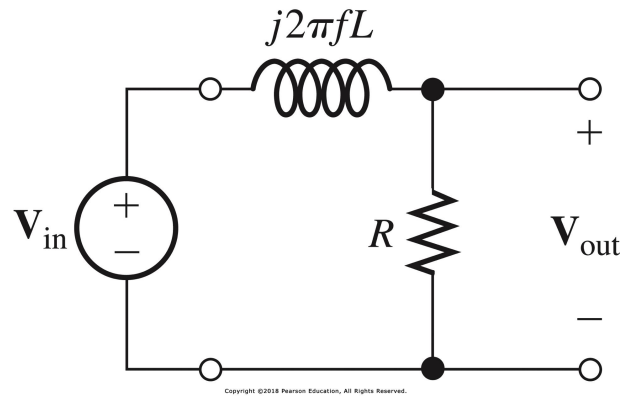
First order High Pass Filter



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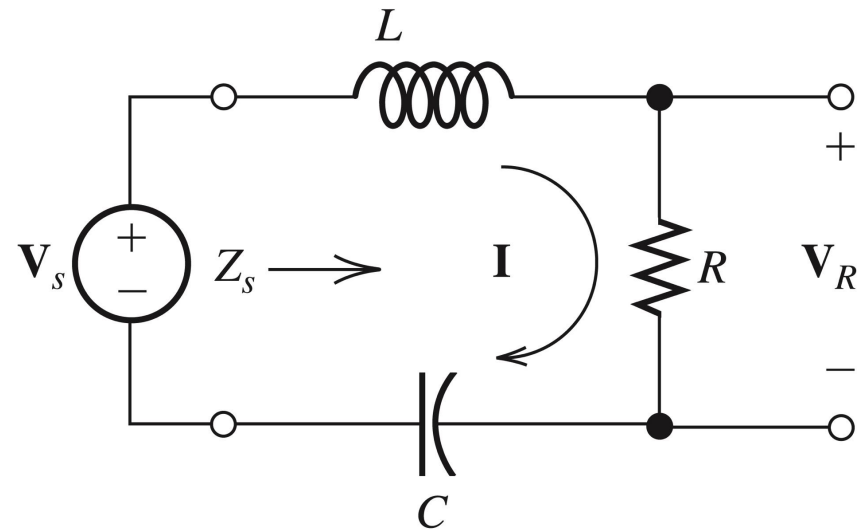
First order High Pass Filter

Low Pass and High Pass Filters with Inductors



Resonant Circuits

Series Resonance



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Recap: R-L-C circuits: Response in time

$$\frac{d^2 v_c}{dt^2} + \frac{1}{(L/R)} \frac{dv_c}{dt} + \frac{1}{LC} v_c = v_s$$

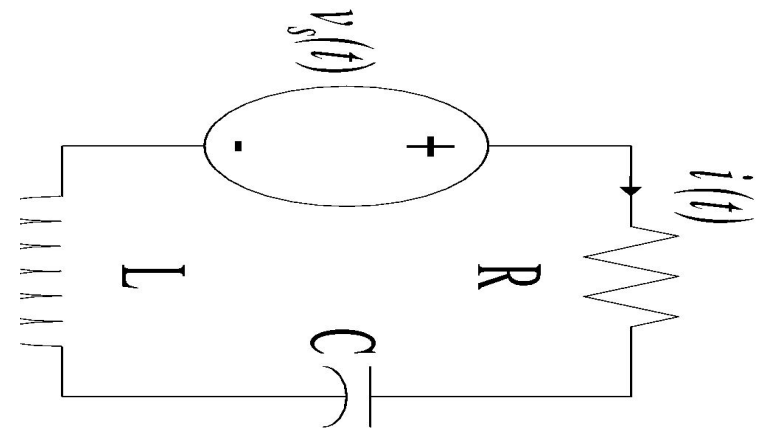
$$\frac{d^2 v_c}{dt^2} + 2\alpha \frac{dv_c}{dt} + \omega_0^2 v_c = v_s$$

Homogeneous solution

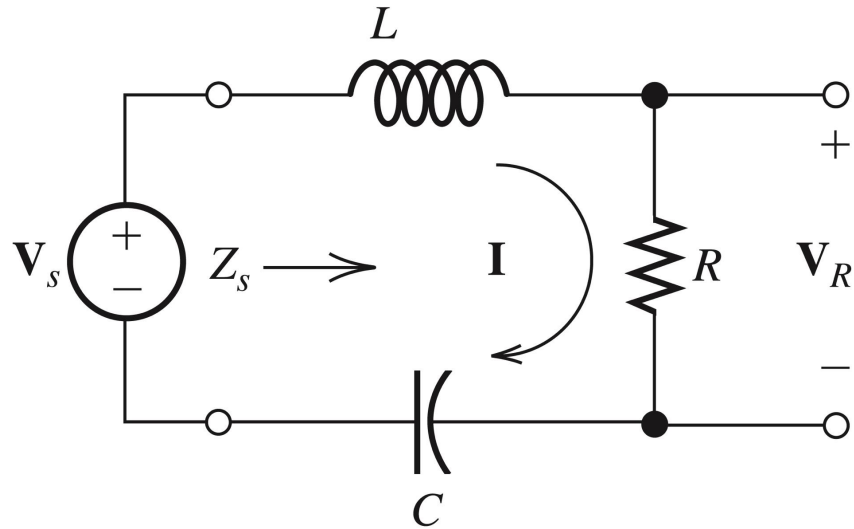
$$\frac{d^2 v_c}{dt^2} + 2\alpha \frac{dv_c}{dt} + \omega_0^2 v_c = 0$$

From previous discussions we have seen that an exponential solution works

Lets try: $v_c(t) = Ae^{st}$



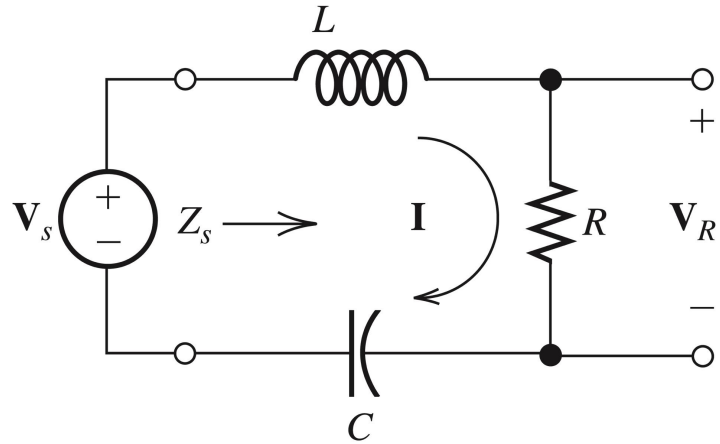
Series Resonance



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$$Z = R + j\omega L - \frac{j}{\omega C}$$

Series Resonance



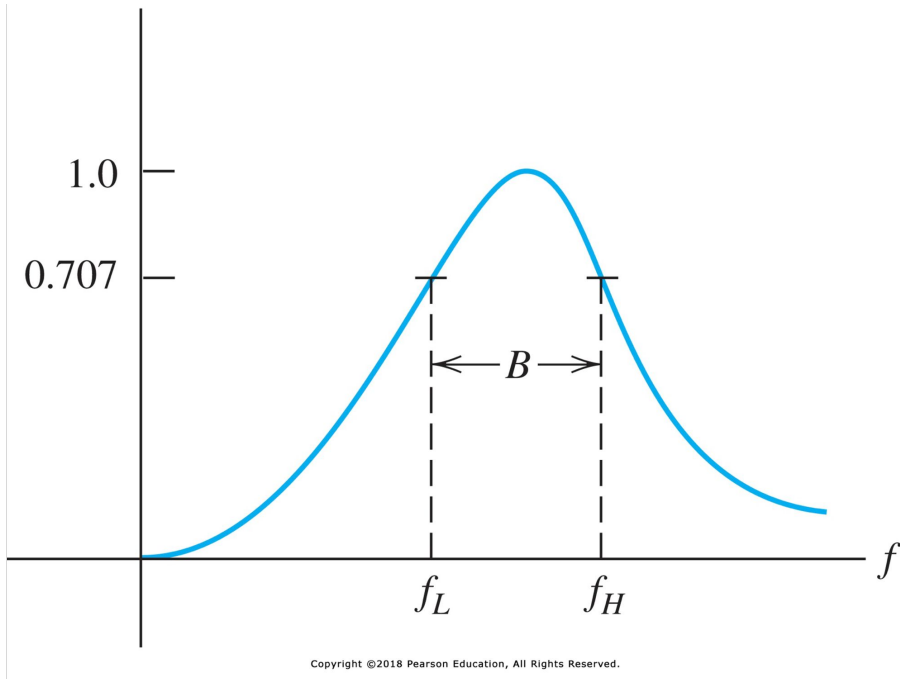
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Series Resonance

Series Resonance

Series Resonance

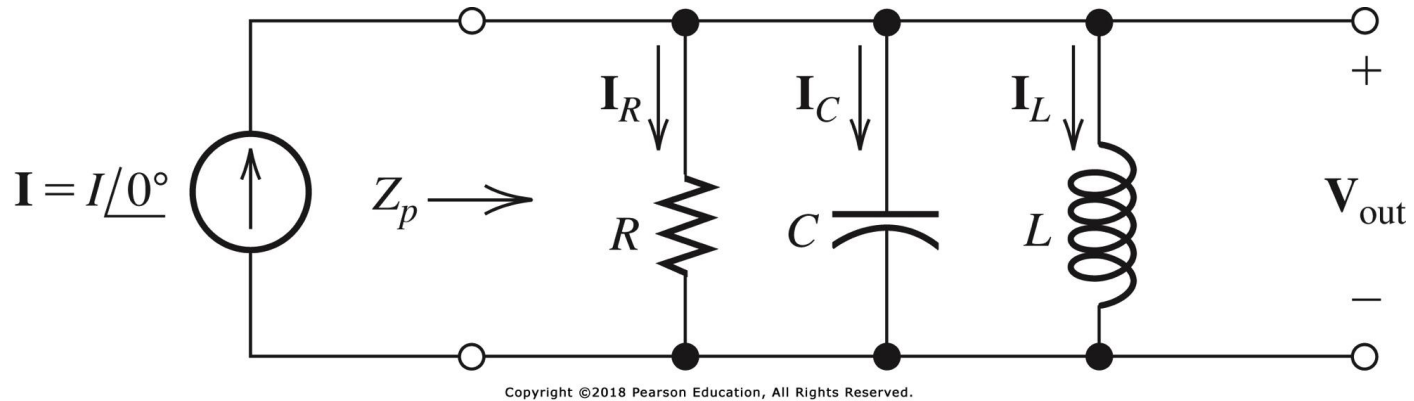
Series Resonance Bandpass Filter



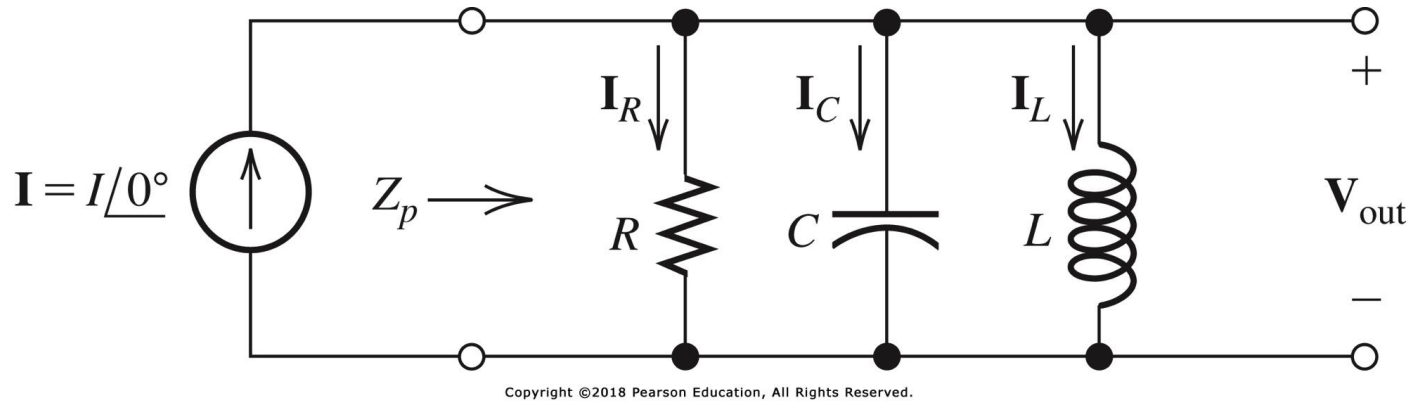
Half-power frequencies are defined as the frequencies where the magnitude of the transfer function has fallen by a factor of $\frac{1}{\sqrt{2}} = 0.707$

It can be shown that
$$B = f_H - f_L = \frac{f_0}{Q_s}$$

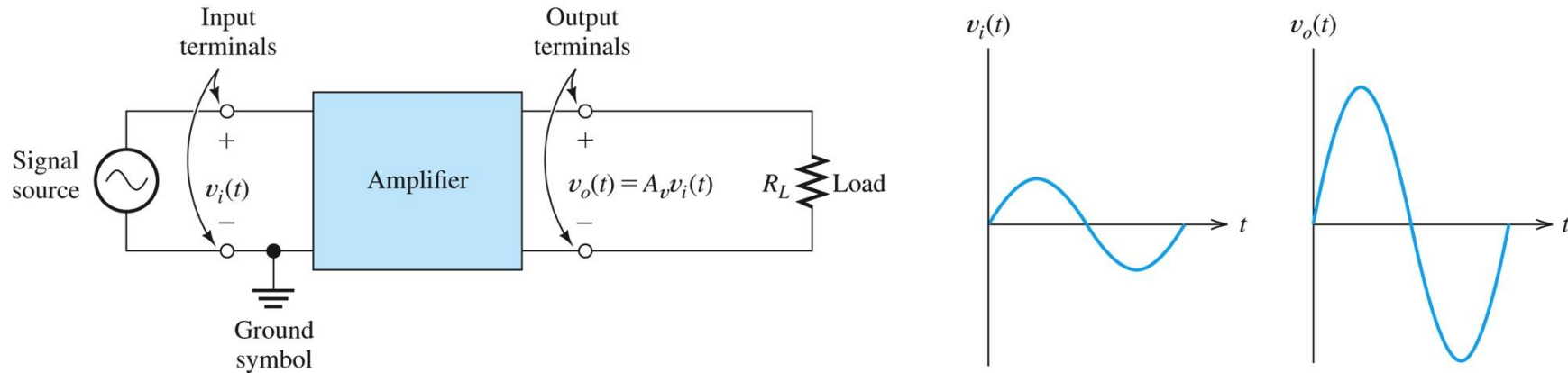
Parallel Resonance



Parallel Resonance



Active Devices



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- Active devices are made of semiconductors
 - Semi-conductors are materials whose resistance is in between a metal and insulator
- Half
- More interestingly, one is able to change the resistance of the semiconductor materials by using external control such as voltage or current

Semiconductors

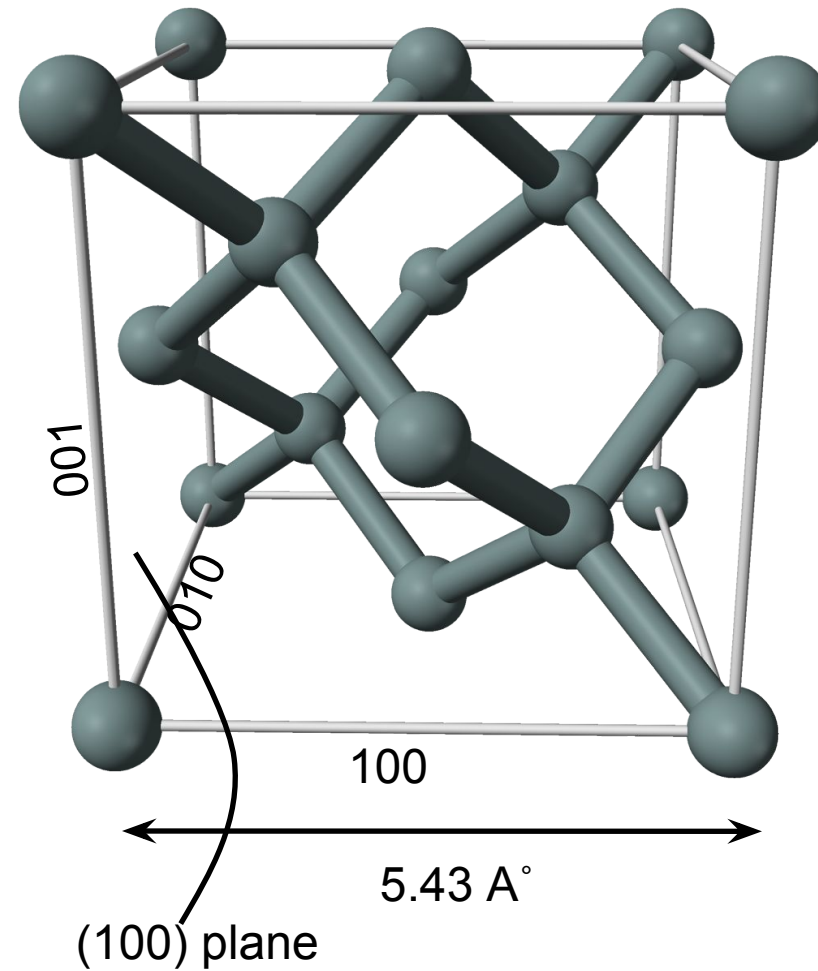
- Semiconductors are **usually** made of group IV elements- atoms that contain, on average, four valence electrons
- Most Common semiconductor used in electronic devices is **Silicon**

Periodic Table of the Elements

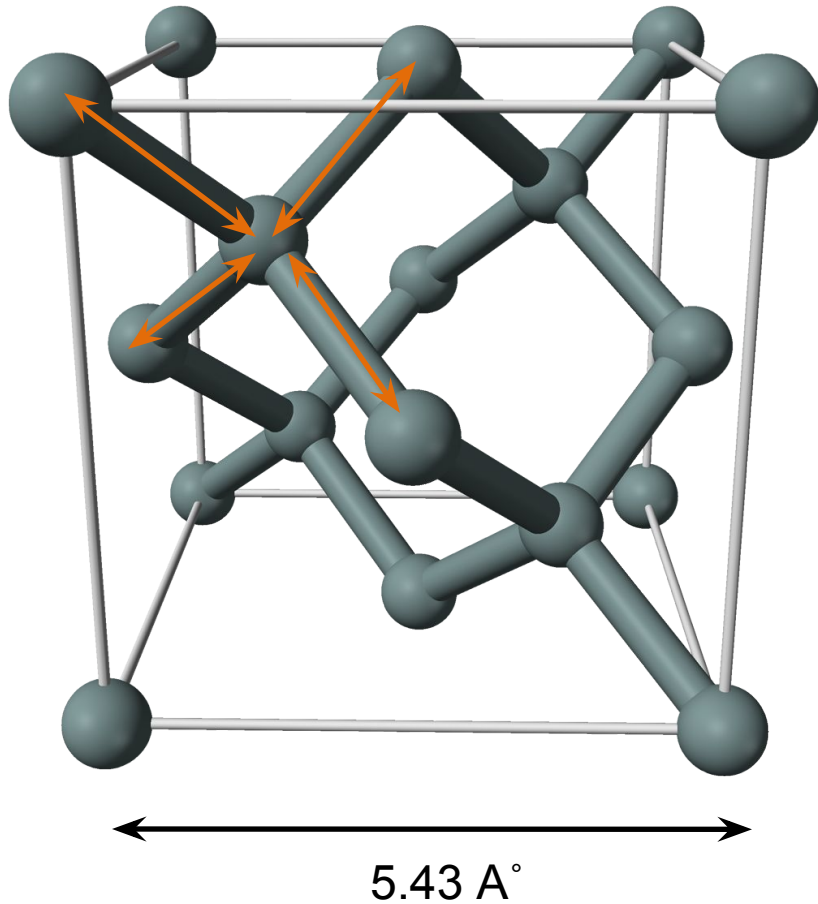
IA																	O	
1	H															He		
IIA												III A	IV A	V A	VIA	VII A		
2	Li	Be											B	C	N	O	F	Ne
3	Na	Mg	IIIB	IVB	VB	VIB	VII B	VIII	VII	IB	IIB	Al	Si	P	S	Cl	Ar	
4	K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr
5	Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe
6	Cs	Ba	*La	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn
7	Fr	Ra	+Ac	Rf	Ha	Sg	Ns	Hs	Mt	110	111	112	113					

Crystal Structure of Si

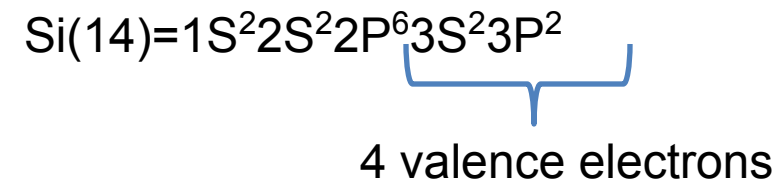
Often known as the diamond lattice



Crystal Structure of Si



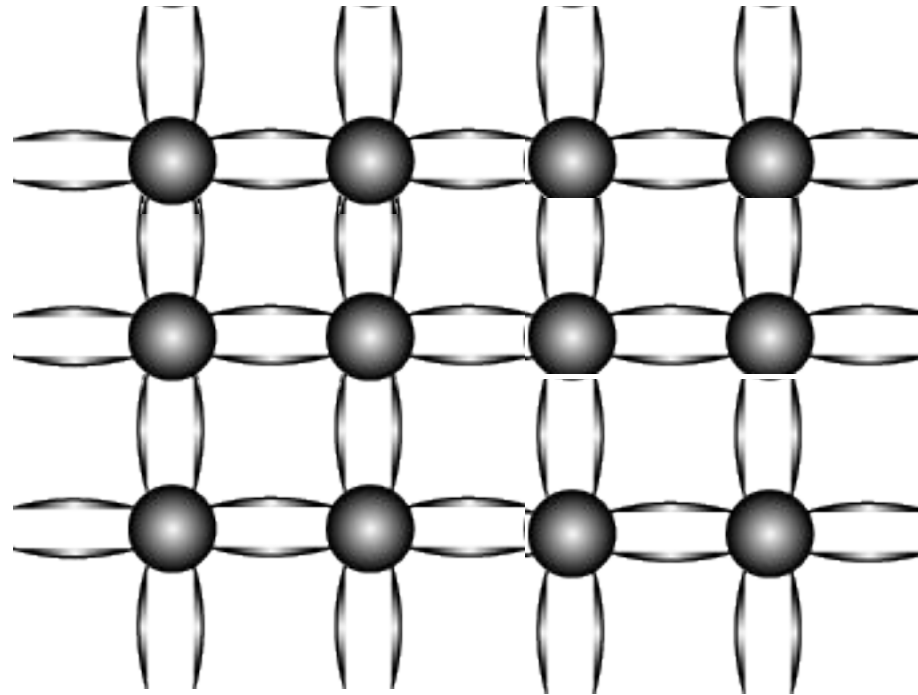
Each atom has 4 nearest neighbors



Each atom shares 2 electrons with 4 nearest neighbors to form a covalent bond

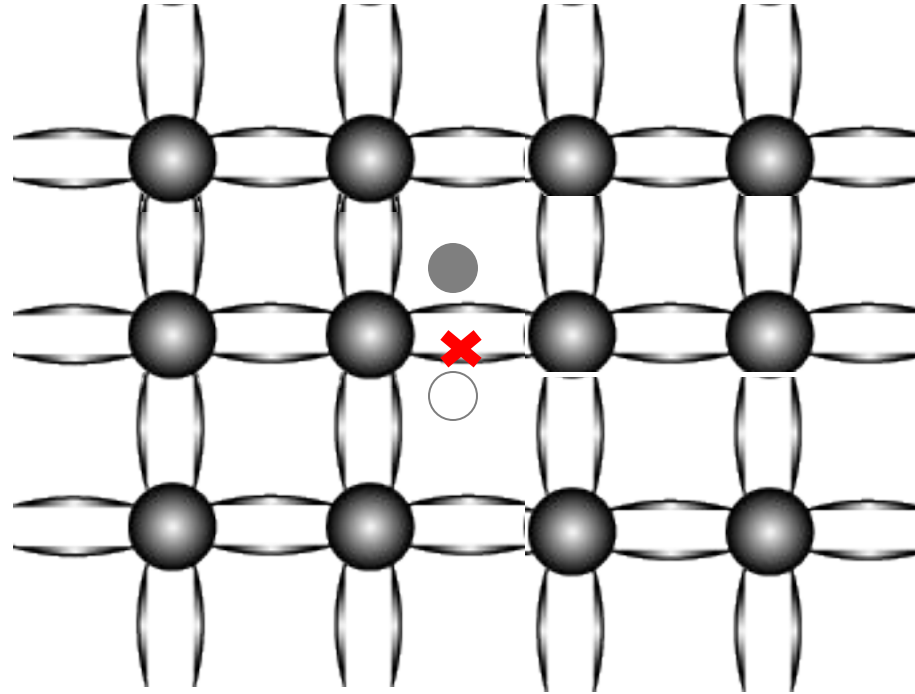
The Bond Model

Each atom shares 2 electrons with 4 nearest neighbors to form a covalent bond



At $T=0\text{K}$, all bonds are satisfied, there are no free carriers, no current flows, looks like an insulator

Intrinsic Si: The Bond Model: Electrons



At finite temperature, an electron may gain enough energy to break the covalent bond, become free and move around.